

Data Sheet	January 2002	

15A, 1000V Ultrafast Diode

The RURP15100 is an ultrafast diode with soft recovery characteristics ($t_{rr} < 100$ ns). It has a low forward voltage drop and is of silicon nitride passivated, ion-implanted, epitaxial construction.

This device is intended for use as a freewheel/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor.

Formerly developmental type TA09906.

Ordering Information

PART NUMBER	PACKAGE	BRAND	
RURP15100	TO-220AC	RURP15100	

NOTE: When ordering, use the entire part number.

Symbol



Features

Ultrafast with Soft Recovery	100ns
Operating Temperature	75 ⁰ C
Reverse Voltage	V000
Avalanche Energy Rated	

Planar Construction

• Planar Constructio

Applications

- · Switching Power Supply
- · Power Switching Circuits
- · General Purpose

Packaging

JEDEC TO-220AC



Absolute Maximum Ratings T _C = 25°C, Unless Otherwise Specified		
	RURP15100	UNITS
Peak Repetitive Reverse Voltage	1000	V
Working Peak Reverse Voltage	1000	V
DC Blocking VoltageV _R	1000	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 142^{\circ}C$)	15	Α
Repetitive Peak Surge Current	30	Α
Nonrepetitive Peak Surge Current	200	Α
Maximum Power Dissipation	100	W
Avalanche Energy (See Figures 7 and 8)	20	mJ
Operating and Storage Temperature	-65 to 175	°C

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified.

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 15A	-	-	1.8	V
	I _F = 15A, T _C = 150°C	-	-	1.5	V
I _R	V _R = 1000V	-	-	100	μА
	V _R = 1000V, T _C = 150°C	-	-	500	μА
t _{rr}	$I_F = 1A$, $dI_F/dt = 100A/\mu s$	-	-	100	ns
	$I_F = 15A$, $dI_F/dt = 100A/\mu s$	-	-	125	ns
t _a	$I_F = 15A$, $dI_F/dt = 100A/\mu s$	-	75	-	ns
t _b	$I_F = 15A$, $dI_F/dt = 100A/\mu s$	-	40	-	ns
$R_{ heta JC}$		-	-	1.5	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time at dI_F/dt = 100A/ μ s (See Figure 6), summation of $t_a + t_b$.

 t_a = Time to reach peak reverse current at dI_F/dt = 100A/ μ s (See Figure 6).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

Typical Performance Curves

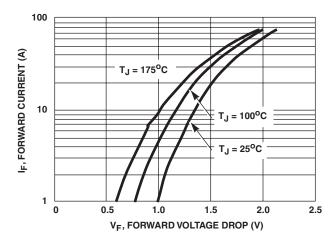


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

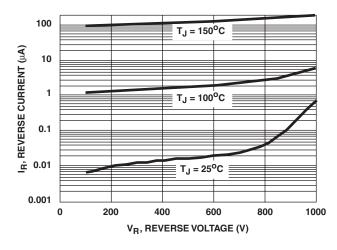


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

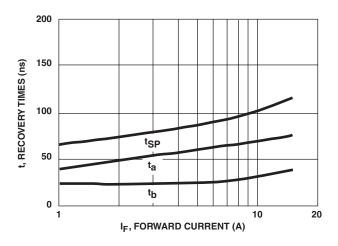


FIGURE 3. $t_{\rm rr}, t_{\rm a}$ AND $t_{\rm b}$ CURVES vs FORWARD CURRENT

16 14 14 12 DC COBBENT 12 DC SQUARE WAVE 8 SQUARE WAVE 2 120 130 140 150 160 170 180 T_C, CASE TEMPERATURE (°C)

FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

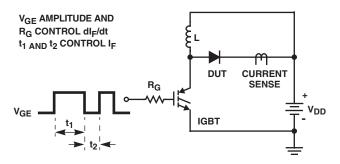


FIGURE 5. t_{rr} TEST CIRCUIT

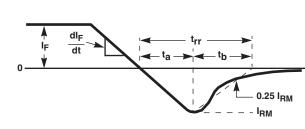


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

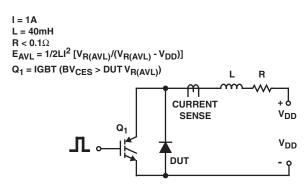


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

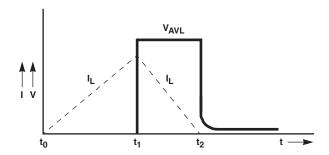


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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PRODUCT STATUS DEFINITIONS

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